CONFIDENTIAL

ELS series
Application data

Dry Powder HSQ "AQM H-SiOx" の描画結果

(2021/07/21)

ELIONIX

営業本部　微細加工部

Conditions

■ Condition for 100 ~ 500 nm Pattern

Substrate: Si

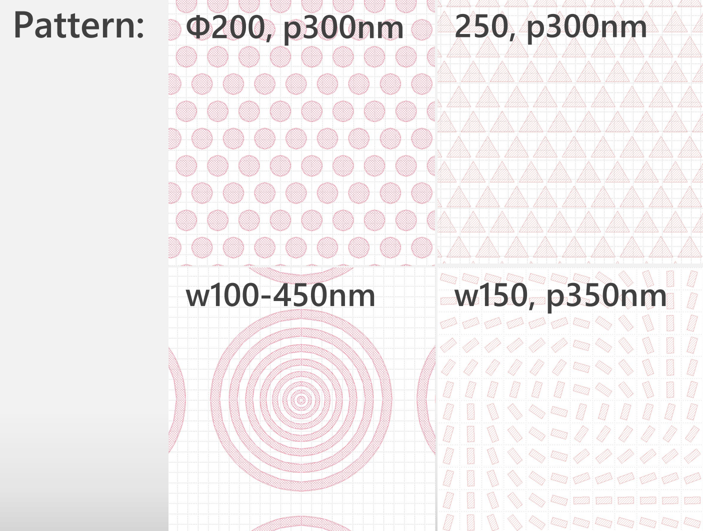
Resist: H-SiOx, 330 nm

Tool: ELS-BODEN

V_{acc}: 50 kV

Beam Current: 10 nA

Pattern:



■ Condition for < 20 nm Pattern

Substrate: Si

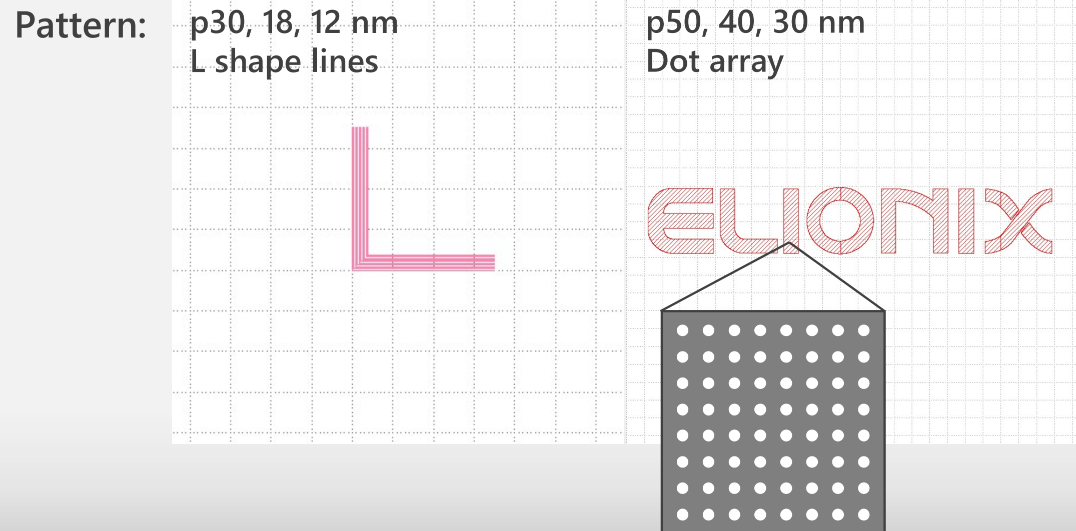
Resist: H-SiOx, 20 nm

Tool: ELS-BODEN

V_{acc}: 150 kV

Beam Current: 100 pA or 1 nA

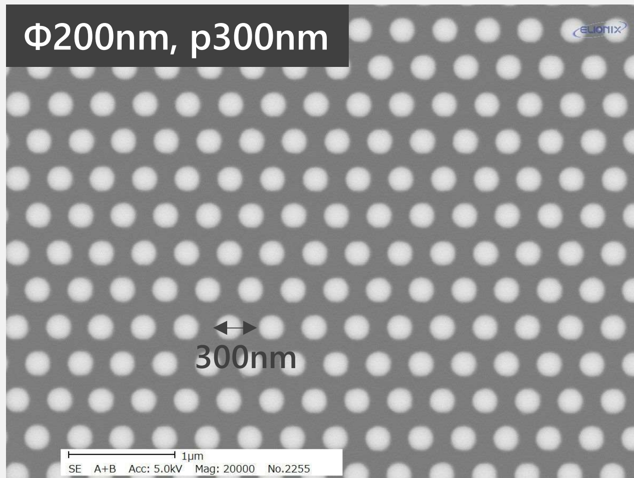
Pattern:

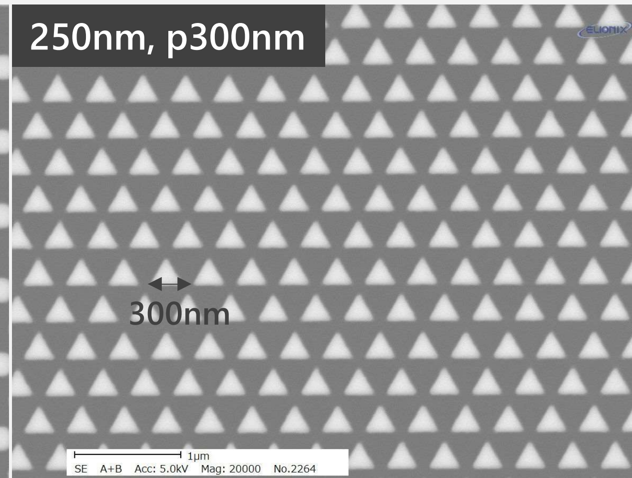


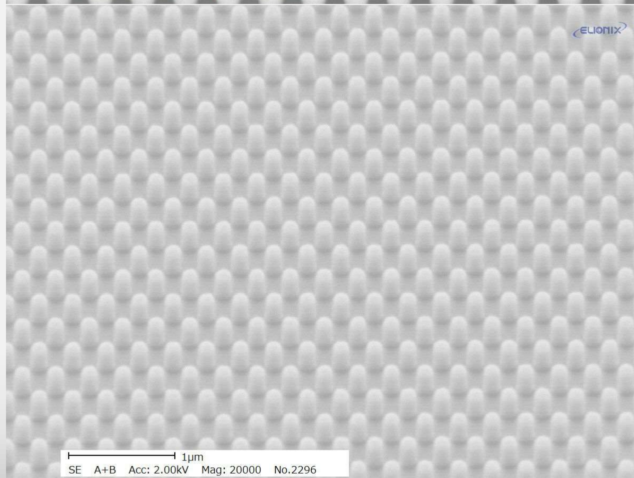
Result 1 - Pattern Size: 100~500 nm -

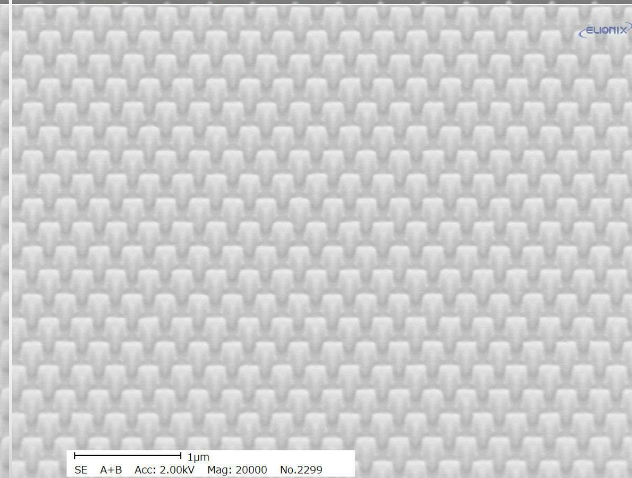
TOP

30° Tilt





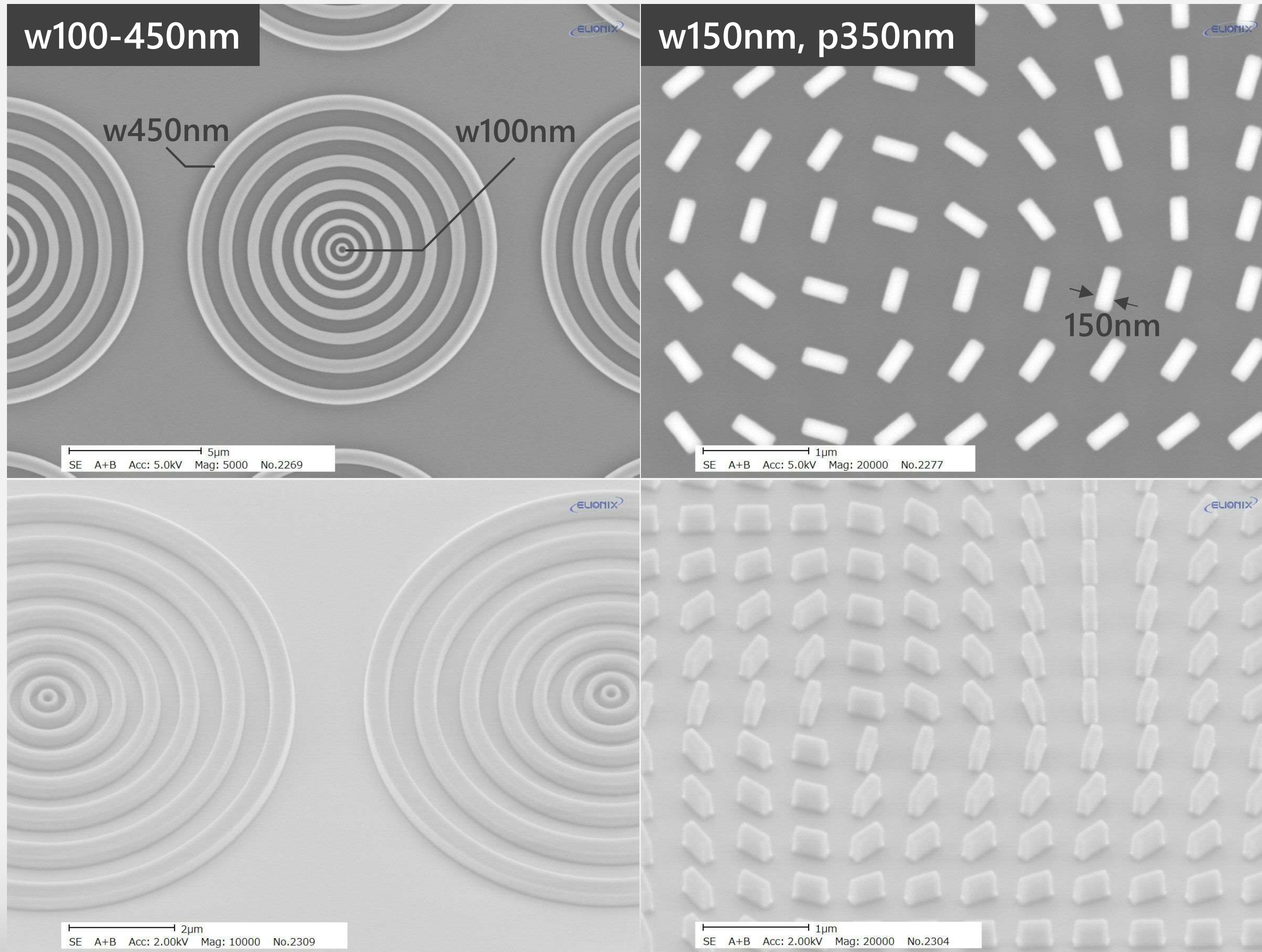




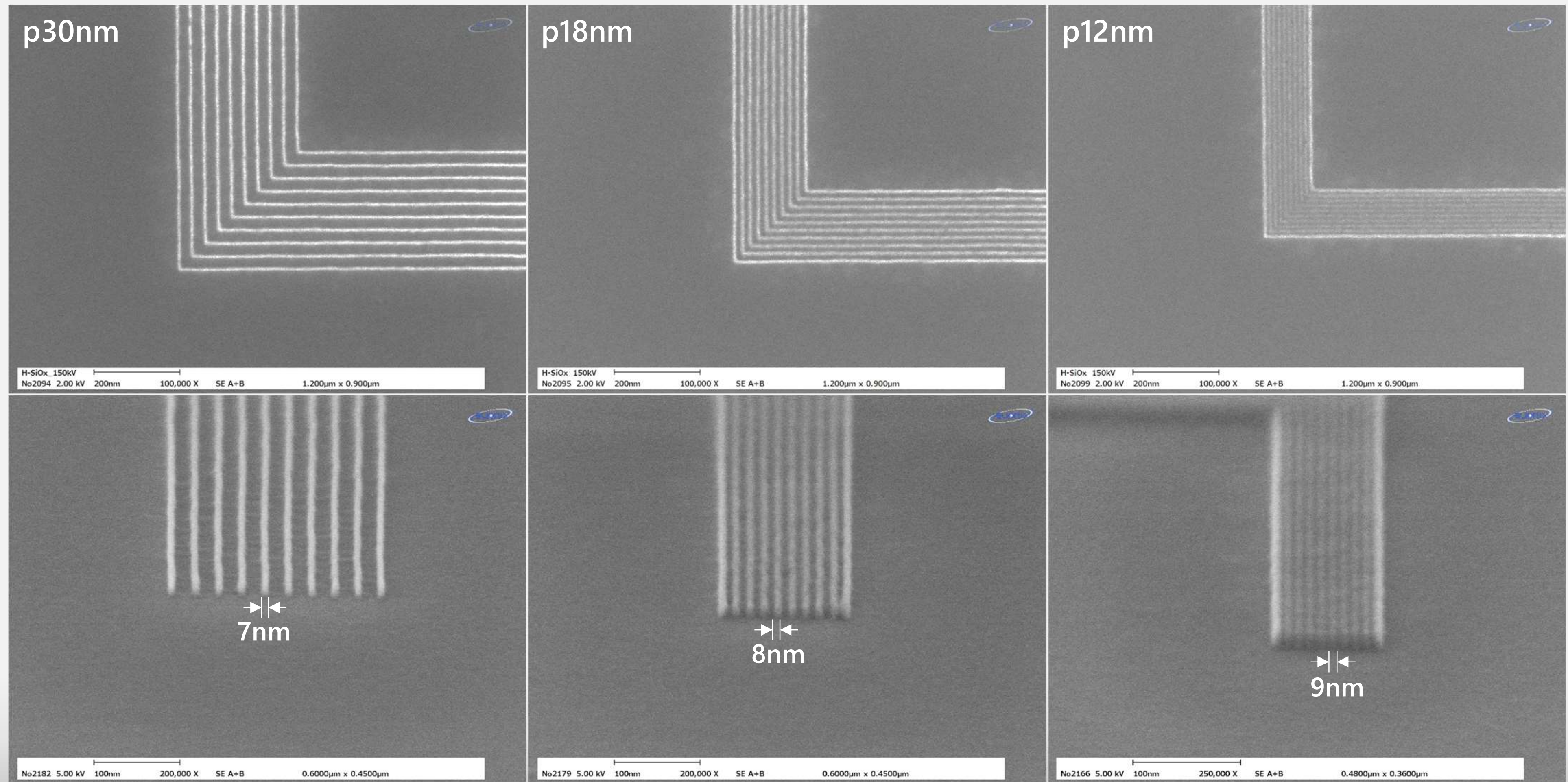
Result 1 - Pattern Size: 100~500 nm -

TOP

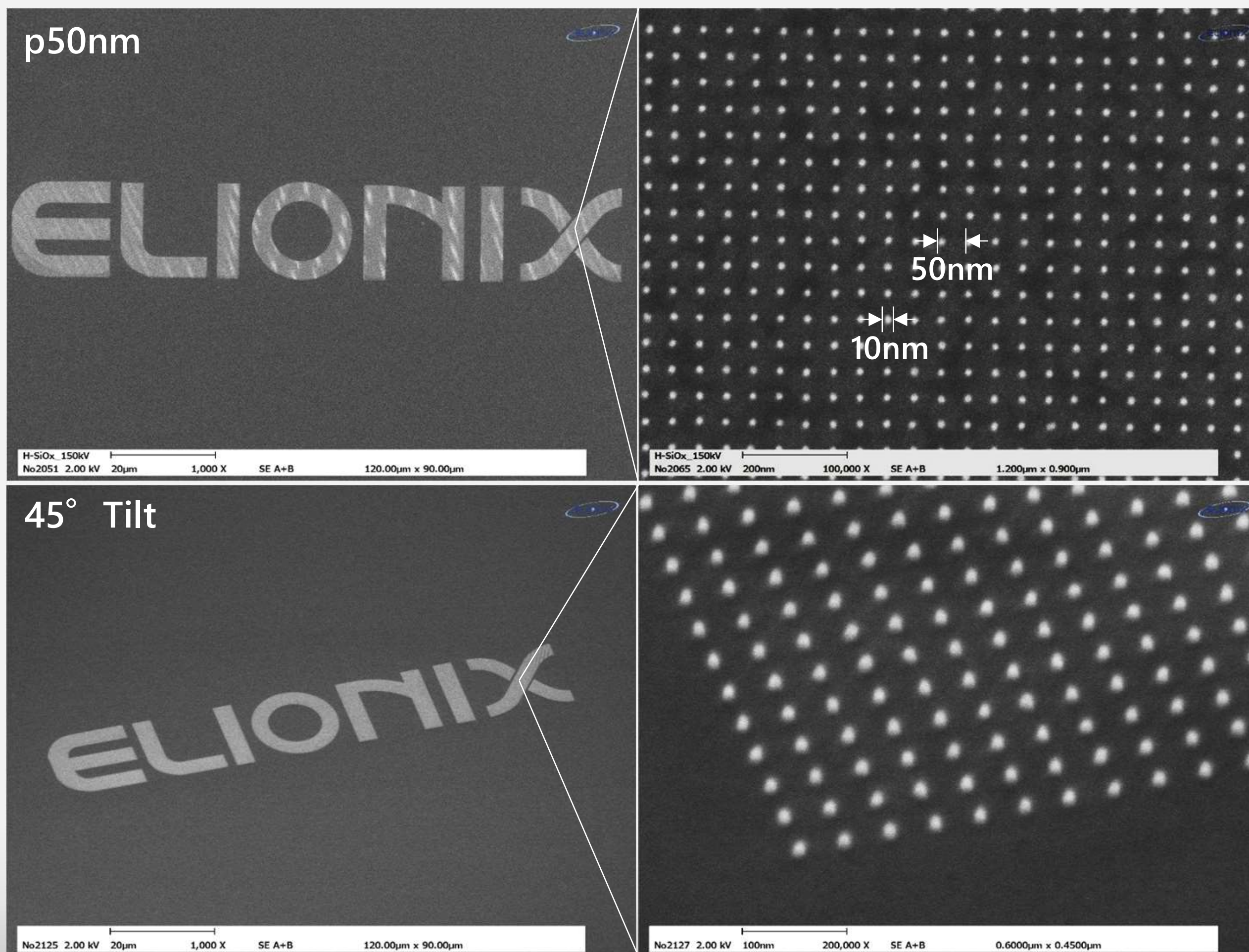
30° Tilt



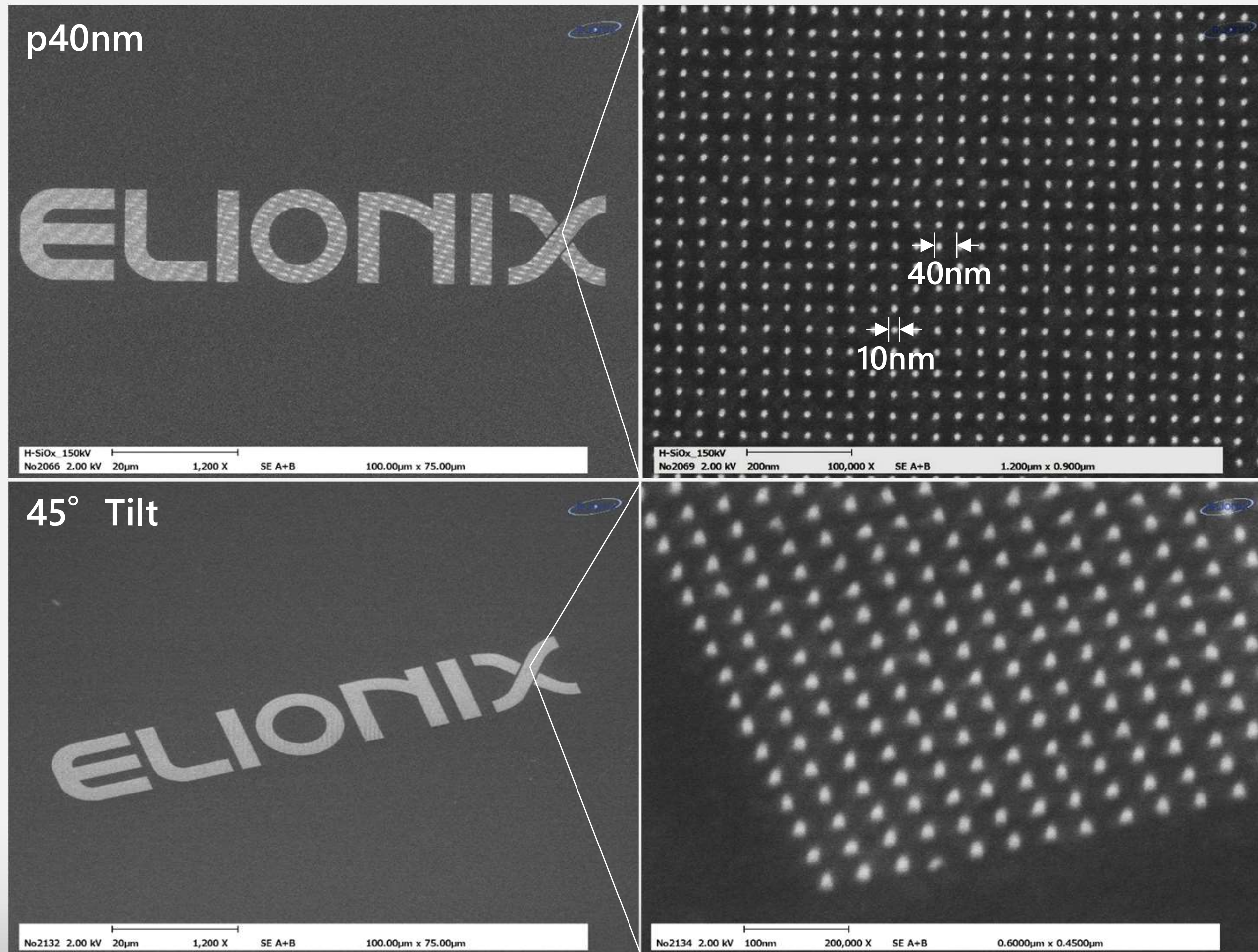
Result 2 - Pattern Size: < 20 nm -



Result 2 - Pattern Size: < 20 nm -



Result 2 - Pattern Size: < 20 nm -



Result 2 - Pattern Size: < 20 nm -